

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,033,642 B2
APPLICATION NO. : 10/666025
DATED : April 25, 2006
INVENTOR(S) : Cem Basceri

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 2, line 9 –

Replace “titanium suicide depositions on separate wafers. For”
Insert --titanium silicide depositions on separate wafers. For--

Col. 2, line 50 –

Replace “of forming titanium suicide comprising layers on”
Insert --of forming titanium silicide comprising layers on--

Col. 4, line 41 –

Replace “to plasma enhance chemical vapor deposit a titanium suicide”
Insert --to plasma enhance chemical vapor deposit a titanium silicide--

Col. 4, line 55 –

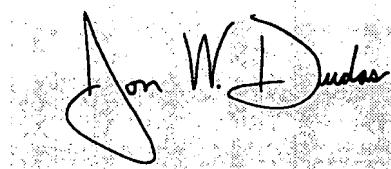
Replace “SiH₄ at from 0.5 sccm to 10 sccm, TiCl₄ at from 50 sccm to”
Insert --SiH₄ at from 0.5 sccm to 10 sccm, TiCl₄ at from 50 sccm to--

Col 4, line 60 –

Replace “vapor deposit a titanium suicide comprising layer which”
Insert --vapor deposit a titanium silicide comprising layer which--

Signed and Sealed this

Third Day of April, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office